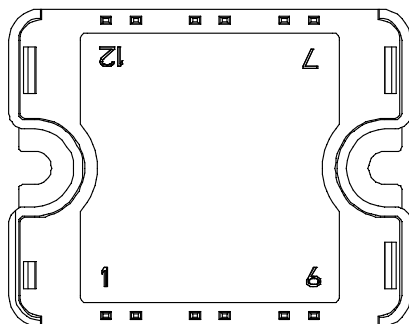
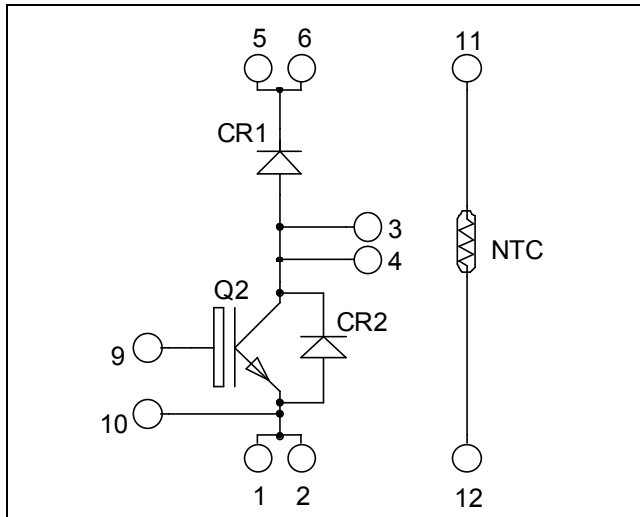


**Boost chopper
High speed Trench + Field Stop IGBT4
Power Module**

**$V_{CES} = 1200V$
 $I_C = 100A @ T_c = 80^\circ C$**



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- **High speed Trench + Field Stop IGBT 4 Technology**
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	A
		$T_C = 80^\circ C$	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	340
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Power Dissipation	520	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			50	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 100A$	$T_j = 25^\circ C$ $T_j = 150^\circ C$	1.78 2.6	2.42	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 3.8 mA$	5.1	5.8	6.4	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		6150		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		460		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		345		
Q_G	Gate charge	$V_{GE} = 15V, I_C = 100A$ $V_{CE} = 960V$		460		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 100A$ $R_G = 5\Omega$		30		ns
T_r	Rise Time			57		
$T_{d(off)}$	Turn-off Delay Time			290		
T_f	Fall Time			16		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 100A$ $R_G = 5\Omega$		30		ns
T_r	Rise Time			49		
$T_{d(off)}$	Turn-off Delay Time			366		
T_f	Fall Time			48		
E_{on}	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 100A$	$T_j = 150^\circ C$	9.5		mJ
E_{off}	Turn off Energy	$R_G = 5\Omega$	$T_j = 150^\circ C$	5.6		
R_G	Integrated gate resistor			7.5		Ω
I_{sc}	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 600V$ $t_p \leq 10\mu s; T_j = 150^\circ C$		350		A
R_{thJC}	Junction to Case Thermal Resistance				0.29	$^\circ C/W$

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage				1200	V
I_{RM}	Reverse Leakage Current	$V_R = 1200V$			100	μA
I_F	DC Forward Current	$T_c = 60^\circ C$		100		A
V_F	Diode Forward Voltage	$I_F = 100A$		2.4	3.5	V
		$I_F = 150A$		2.7		
		$I_F = 100A$ $T_j = 125^\circ C$		1.8		
t_{rr}	Reverse Recovery Time	$I_F = 100A$ $V_R = 800V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ C$	385		ns
			$T_j = 125^\circ C$	480		
Q_{rr}	Reverse Recovery Charge	$T_j = 25^\circ C$ $T_j = 125^\circ C$		1.05		μC
				5.24		
R_{thJC}	Junction to Case Thermal Resistance				0.35	$^\circ C/W$

IGBT parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage				1200	V
I _{RM}	Reverse Leakage Current	V _R =1200V			100	μA
I _F	DC Forward Current	T _c = 70°C		30		A
V _F	Diode Forward Voltage	I _F = 30A		2.6	3.5	V
		I _F = 60A		3.2		
		I _F = 30A, T _j = 125°C		1.8		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 800V di/dt = 200A/μs	T _j = 25°C	300		ns
			T _j = 125°C	360		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C	360		nC
			T _j = 125°C	1700		
R _{thJC}	Junction to Case Thermal Resistance				1.2	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

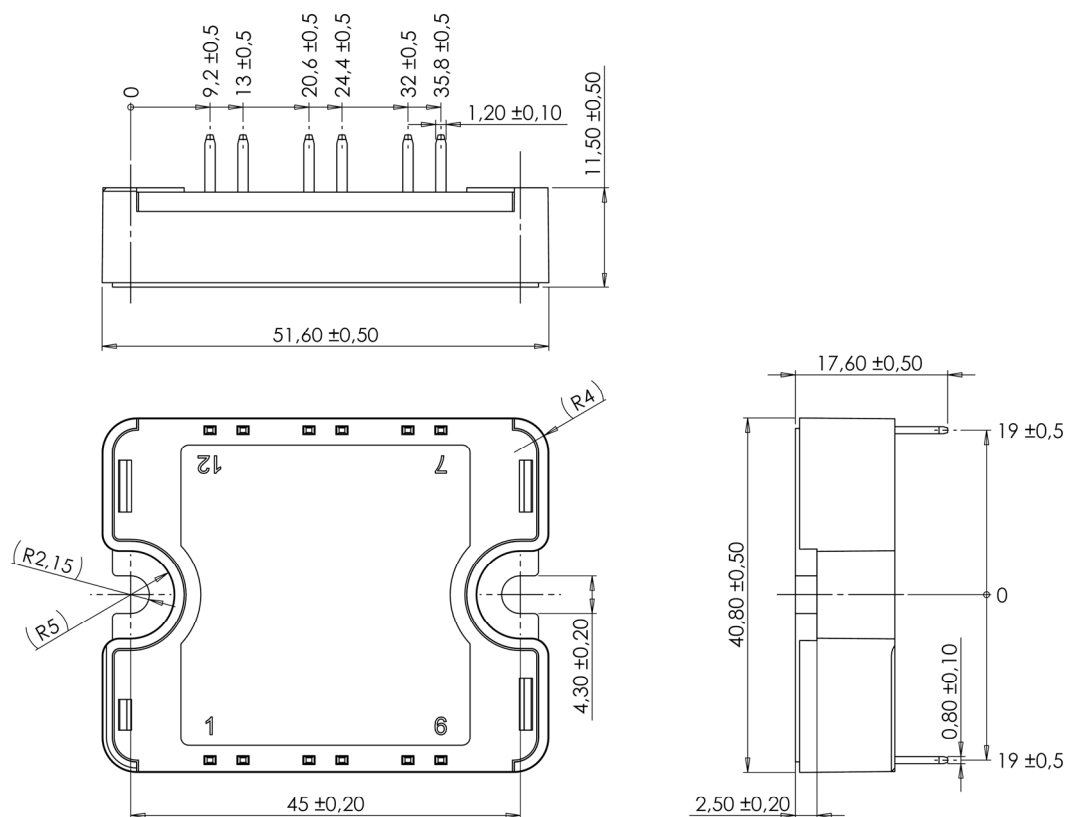
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

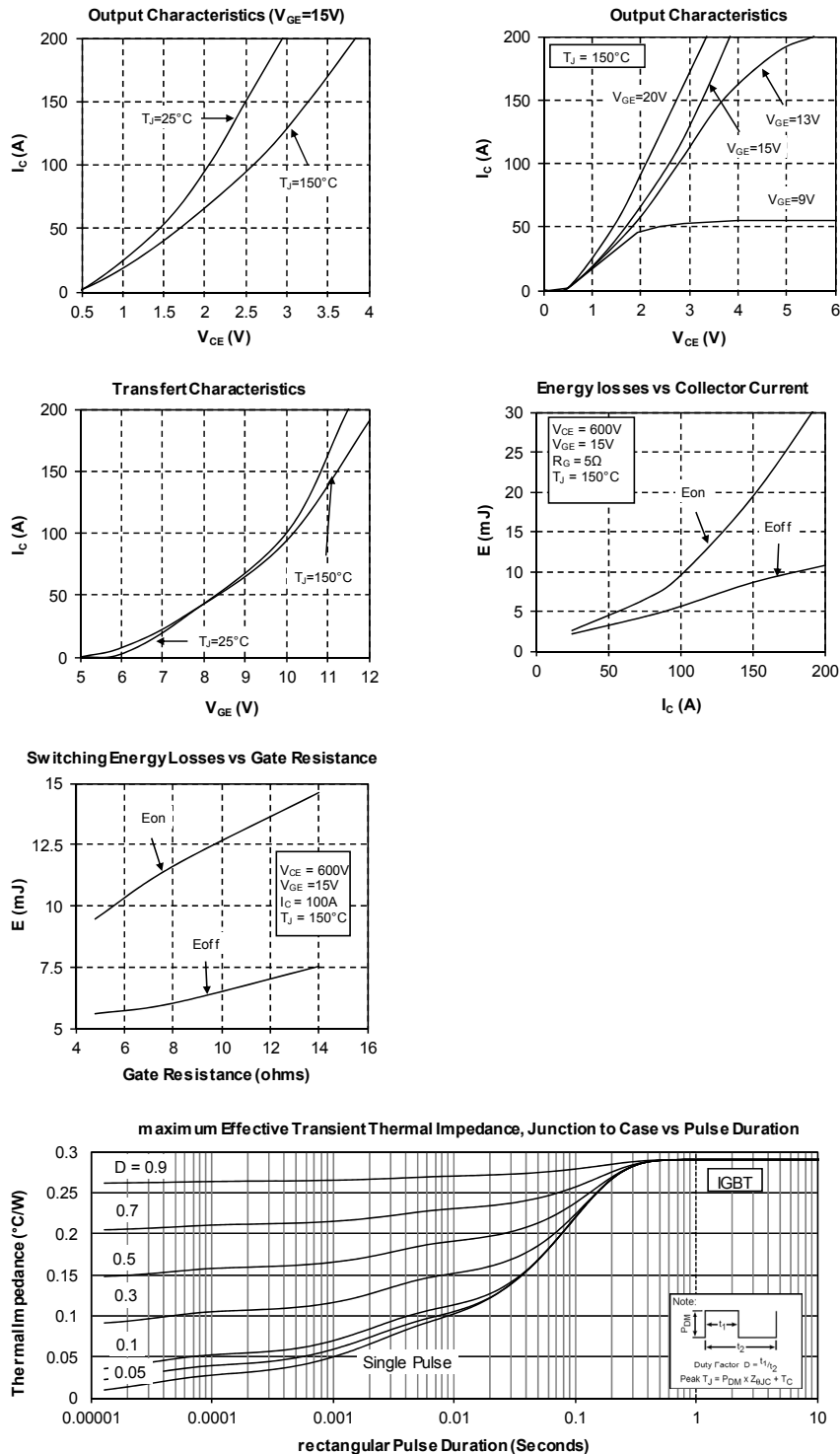
Symbol	Characteristic	Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz	4000		V
T _J	Operating junction temperature range	-40	175	°C
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} -25	
T _{STG}	Storage Temperature Range	-40	125	
T _C	Operating Case Temperature	-40	125	
Torque	Mounting torque	To heatsink	M4	N.m
Wt	Package Weight		80	g

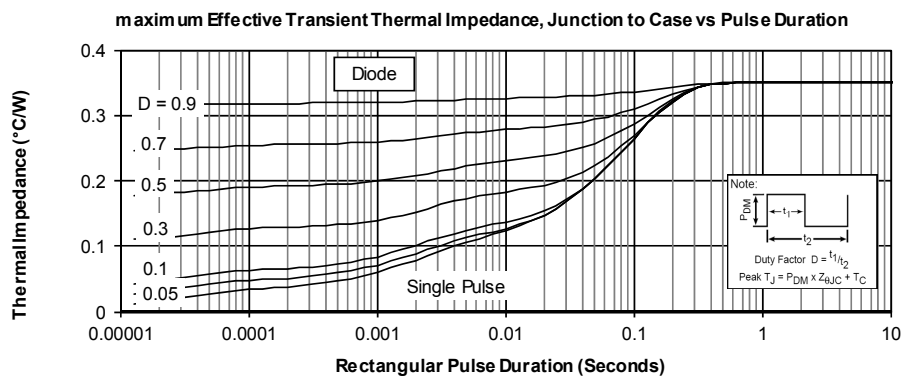
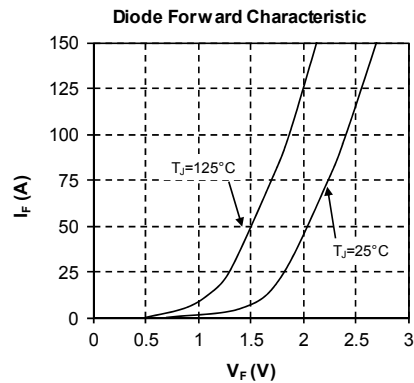
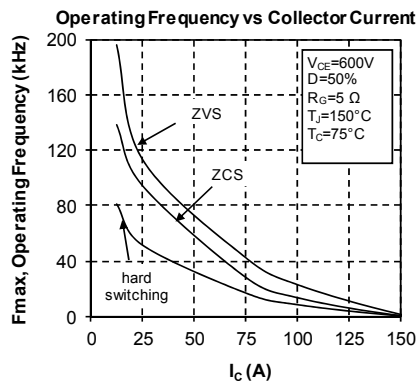
Package outline (dimensions in mm)



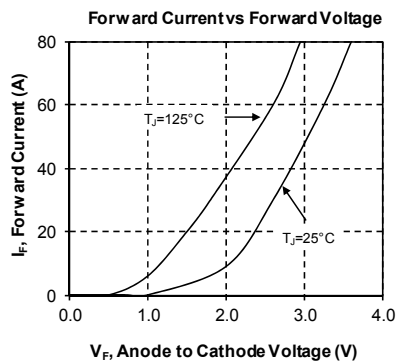
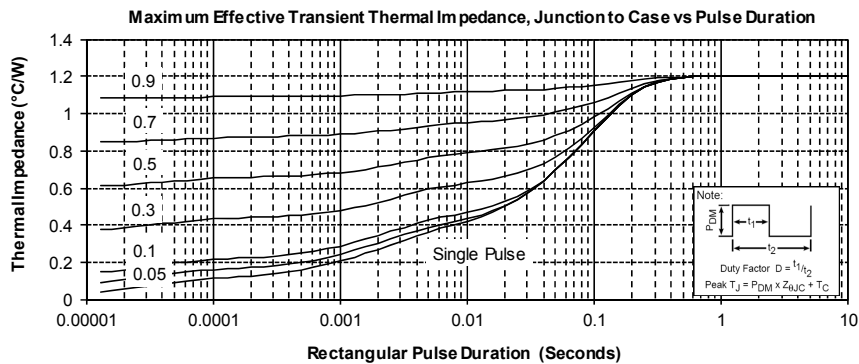
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Typical IGBT & chopper diode performance curves





IGBT parallel diode Typical Performance Curves



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